

/ Descriptions

Silicon PNP transistor in a TO-220F Plastic Package.

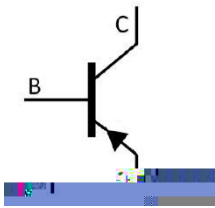
/ Features

Low saturation voltage, complementary to KTD2058.

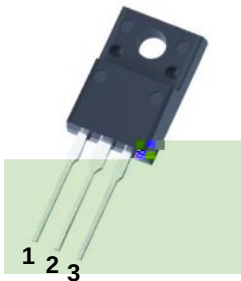
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

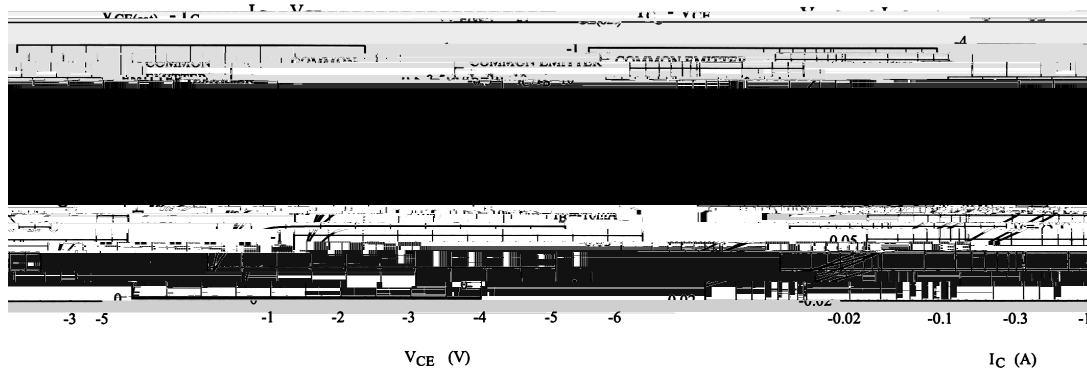
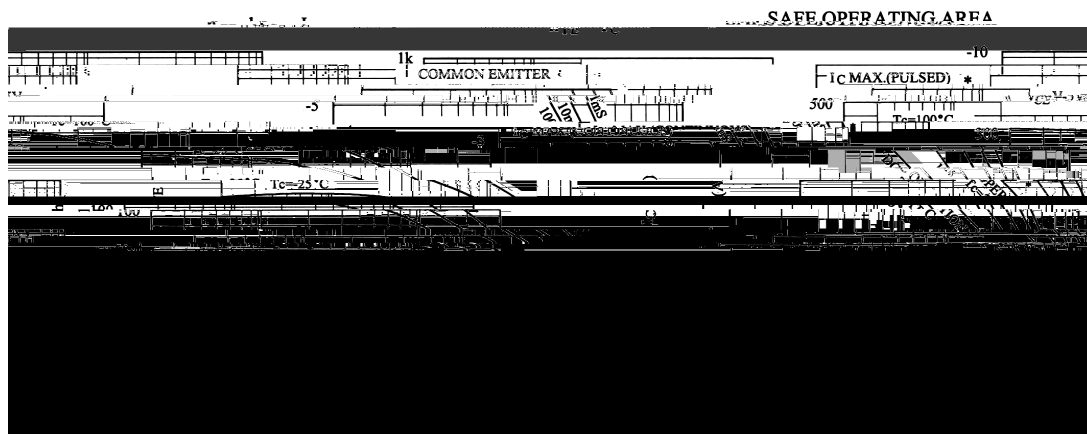
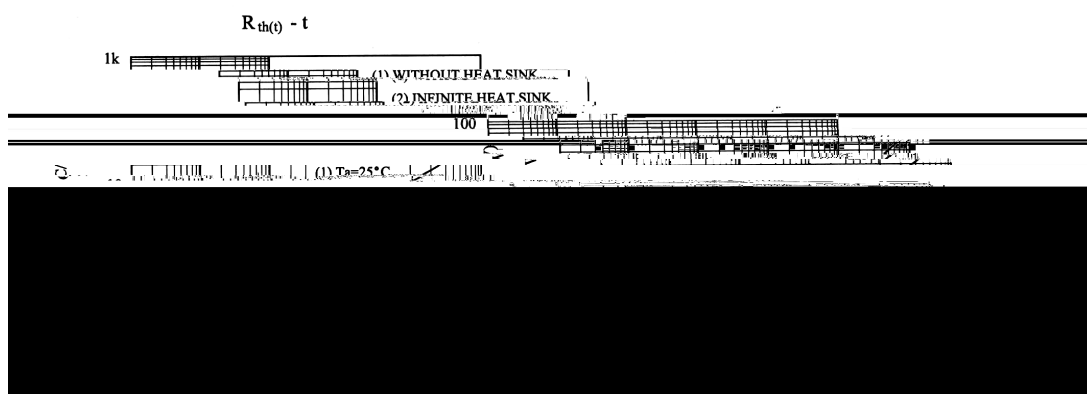
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	60 120	100 200

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current	I_B	-0.5	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter Symbol

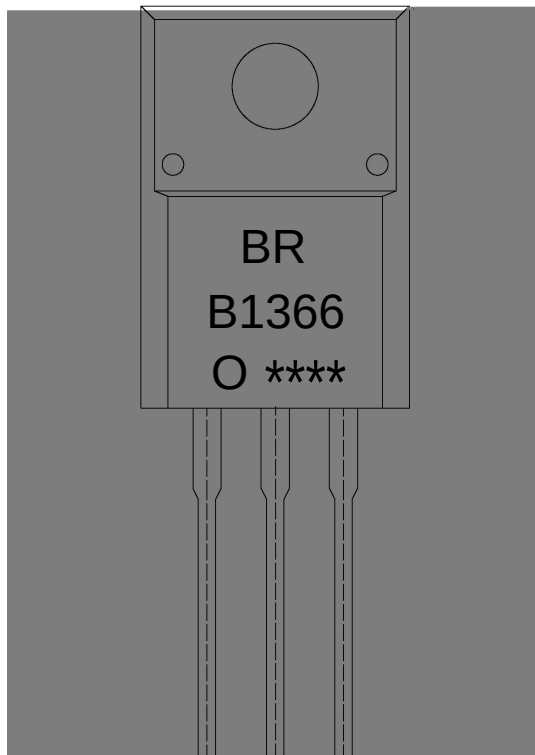
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

B1366

O: h_{FE}

Note:

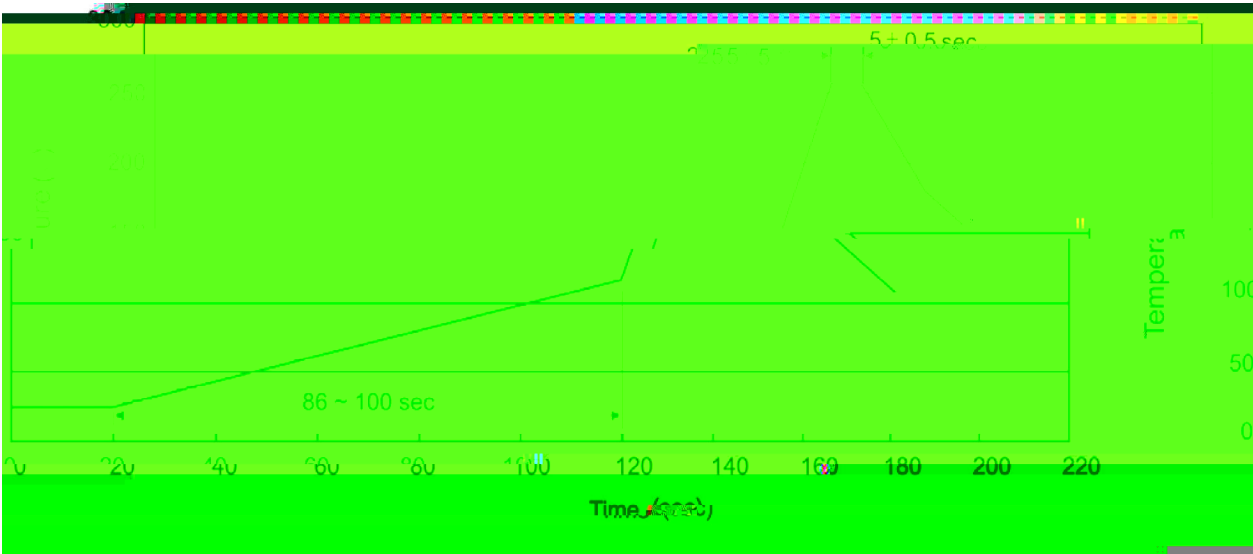
BR: Company Code.

B1366: Product Type.

O: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5

10 1 sec.

Temp:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box